

# 852 nm Grating Stabilized, Single-Frequency Laser Diode



### **Description**

The FPV852S 852 nm, Single-Frequency, Wavelength-Stabilized Laser Diode is based on quantum well epitaxial layer growth and a highly reliable ridge waveguide structure with external volume-holographic-grating (VHG) feedback. This single-frequency laser diode is housed in a butterfly package with an internal optical isolator, monitor diode, TEC and a thermistor that allows the laser to be temperature controlled. This laser diode produces a wavelength-stabilized spectrum with a single-frequency narrow linewidth over the operating power range of approximately 10 to 20 mW. The output is coupled to 1.0 m of FC/APC-terminated 780HP single-mode fiber.

#### **Specifications**

Absolute Maximum Ratings <sup>a</sup>				
LD Reverse Voltage (Max)	2.0 V			
PD Reverse Voltage (Max)	20 V			
Absolute Max Current	400 mA			
Absolute Max Power	30 mW			
Operating Case Temperature	0 to 70 °C			
Storage Temperature	-10 to 70 °C			
Pin Code	14 Pin, Type 1			

a. Do not exceed the maximum optical power or maximum drive current, whichever occurs first.

Characteristics (CW; $T_{CHIP} = T_{CS}$ , $T_{CASE} = 0 - 70 ^{\circ}C$ )					
	Symbol	Min	Typical	Max	
Center Wavelength	λ <sub>C</sub>	851 nm	852 nm	853 nm	
Single Frequency Output Power <sup>a</sup> (CW @ I <sub>CW</sub> and T <sub>CS</sub> )	P <sub>CW-SF</sub>	18 mW	20 mW	-	
Single Frequency Power Range	$\Delta P_{SF}$	10 mW <sup>b</sup>	-	-	
Operating Current (CW)	I <sub>cw</sub>	-	-	400 mA	
Center Temperature for $\Delta T_{stabilized}$	T <sub>CS</sub>	20 °C	-	35 °C	
Wavelength-Stabilized Temperature Range	<b>ΔT</b> <sub>stabilized</sub>	5 °C	-	-	
Threshold Current	I <sub>TH</sub>	-	50 mA	100 mA	
Side Mode Suppression Ratio (SMSR)	SMSR	25 dB	40 dB	-	
Internal Isolator Isolation	ISO	35 dB	-	-	
Forward Voltage	$V_{F}$	-	2.2 V	2.8 V	
Laser Linewidth	Δν	-	15 MHz	-	
Monitor Photodiode Current	Iphoto	-	0.3 mA	-	
TEC Operation (Typical/Max @ T <sub>CASE</sub> = 25 °C / 70 °C)					
-TEC Current	I <sub>TEC</sub>	-	0.15 A	1.4 A	
-TEC Voltage	V <sub>TEC</sub>	-	0.4 V	6.0 V	
-Thermistor Resistance	R <sub>TH</sub>	-	10 kΩ	-	

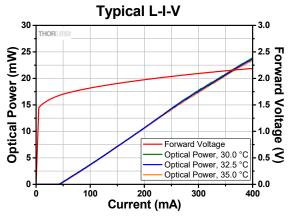
a. This value is the upper limit of the range where the diode can produce a single-frequency output and varies from laser to laser. The performance of each individual laser can be found on the unit-specific data sheet.

b. This value is specified for temperatures in the range given by  $T_{CS} \pm 1/2\Delta T_{stabilized}$ . The 10 mW minimum single frequency power range corresponds to output powers between the typical  $P_{CW-SF} - \Delta P_{SF}$  and  $P_{CW-SF}$ , i.e., between 10 mW and 20 mW.

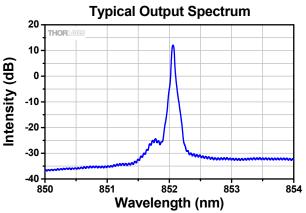


### **Typical Performance Plots**

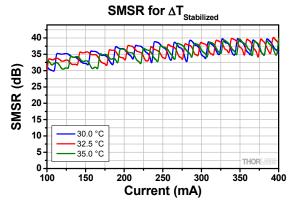
The plots below are typical; performance will vary between individual lasers. Each laser includes a serial-number-specific datasheet detailing performance.



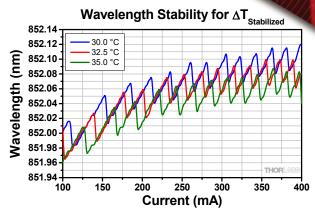
The typical output power vs. current is shown for three temperatures within the wavelength stabilized temperature range ( $\Delta T_{stabilized}$ ) of a FPV852S laser diode.



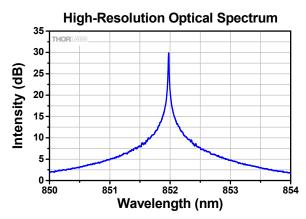
The typical optical spectrum is shown above. The data was obtained with a 350 mA drive current and the device held at 25  $^{\circ}$  C.



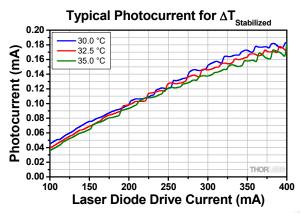
The typical side mode suppression ratio (SMSR) is shown for three temperatures within the wavelength stabilized temperature range ( $\Delta T_{stabilized}$ ).



When used within the wavelength stabilized temperature range ( $\Delta T_{stabilized}$ ), the FPV852S laser shows excellent wavelength stability over a range of drive currents.



This high-resolution optical spectrum was obtained using one of Thorlabs' Optical Spectrum Analyzers (OSA201C), which provides 8 pm resolution at 852 nm.



The typical monitor photodiode current over laser diode current is shown above.



## **Drawing**

